



2SC1061

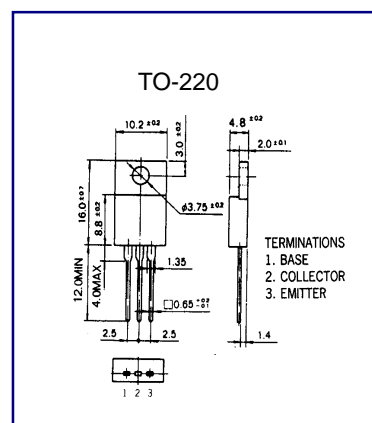
NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SA671

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

| Characteristic | Symbol | Rating | Unit |
|--|-----------|---------|------------------|
| Collector-Base Voltage | V_{CB0} | 50 | V |
| Collector-Emitter Voltage | V_{CE0} | 50 | V |
| Emitter-Base voltage | V_{EB0} | 7 | V |
| Collector Current (DC) | I_C | 3 | A |
| Collector Dissipation ($T_c=25^\circ\text{C}$) | P_C | 25 | W |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -50~150 | $^\circ\text{C}$ |



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|---------------------------------------|---------------|--|-----|-----|-----|---------------|
| Collector Cutoff Current | I_{CBO} | $V_{CB}=50\text{V}$, $I_E=0$ | | | 100 | μA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB}=7\text{V}$, $I_C=0$ | | | 100 | μA |
| DC Current Gain | h_{FE1} | $V_{CE}=4\text{V}$, $I_C=1\text{A}$ | 35 | | 200 | |
| Collector- Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C=3\text{A}$, $I_B=0.3\text{A}$ | | | 1.0 | V |
| Current Gain Bandwidth Product | f_T | $V_{CE}=5\text{V}$, $I_C=0.5\text{A}$ | | 8 | | MHZ |